



DMT10H009SK3

Product Summary

BV _{DSS}	Rds(on) Max	I⊵ Max Tc = +25°C
100V	9.1mΩ @ V _{GS} = 10V	91A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Features

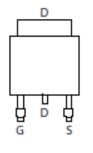
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Qg –Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

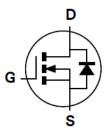
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



Equivalent Circuit

Ordering Information (Note 4)

Case	Packaging
TO252 (DPAK)	2500/Tape & Reel

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

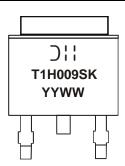
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



J = Manufacturer's Marking
T1H009SK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current Mar. 10M	Tc = +25°C	- ID	91	А
Continuous Drain Current, V _{GS} = 10V	$T_{\rm C} = +70^{\circ}{\rm C}$		75	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Ідм	360	A
Maximum Continuous Body Diode Forward Current (Note 6)		ls	91	A
Avalanche Current, L = 3mH (Note 8)		I _{AS}	11	A
Avalanche Energy, L = 3mH (Note 8)		E _{AS}	181	mJ
V _{DS} Spike, L = 0.1mH	t = 10μs	VSPIKE	120	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)		PD	1.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	73	°C/W	
Total Power Dissipation (Note 6)		PD	3.2	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	39	°C/W	
Thermal Resistance, Junction to Case		Rejc	1.1	°C/vv	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

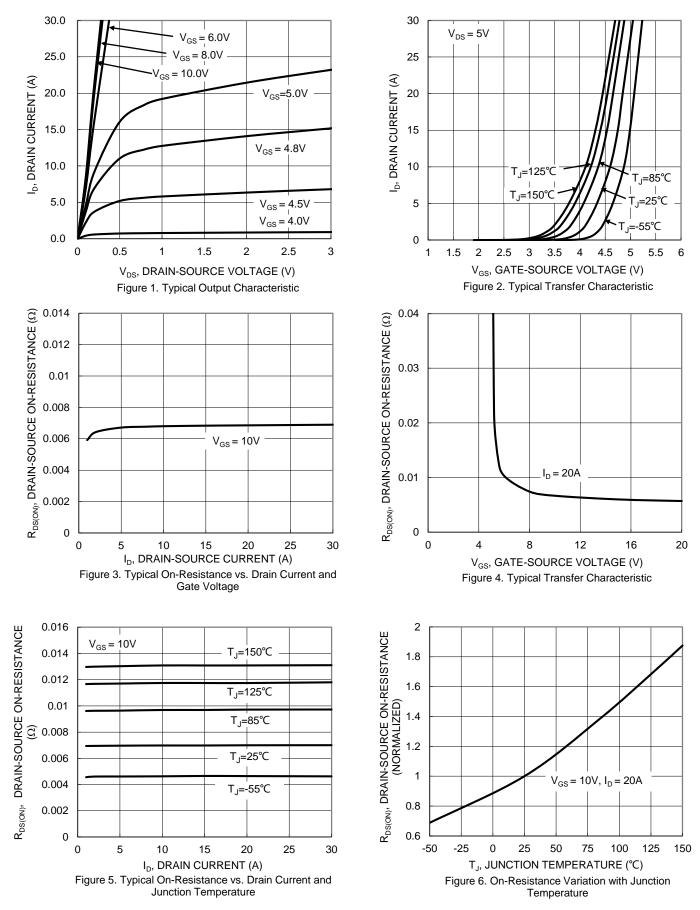
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				1	•		
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA $V_{DS} = 80V, V_{GS} = 0V$		
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	2	_	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	—	6.9	9.1	mΩ	V _{GS} = 10V, I _D = 20A	
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		2028			$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		546		pF		
Reverse Transfer Capacitance	Crss	—	11	_			
Gate Resistance	Rg	0.4	1.7	3.4	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	34	_		$V_{DD} = 50V, I_D = 13A,$ $V_{GS} = 10V$	
Gate-Source Charge	Qgs	_	6	_	nC		
Gate-Drain Charge	Qgd		12				
Turn-On Delay Time	tD(ON)		8.3			$V_{DD} = 50V, V_{GS} = 10V,$ $I_D = 13A, R_g = 6\Omega$	
Turn-On Rise Time	tR		15.9				
Turn-Off Delay Time	tD(OFF)	_	27.6	_	ns		
Turn-Off Fall Time	t _F	_	21.3	—	1		
Reverse Recovery Time	trr	_	47	_	ns		
Reverse Recovery Charge	Q _{RR}	_	72	_	nC	IF = 13A, di/dt = 100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:



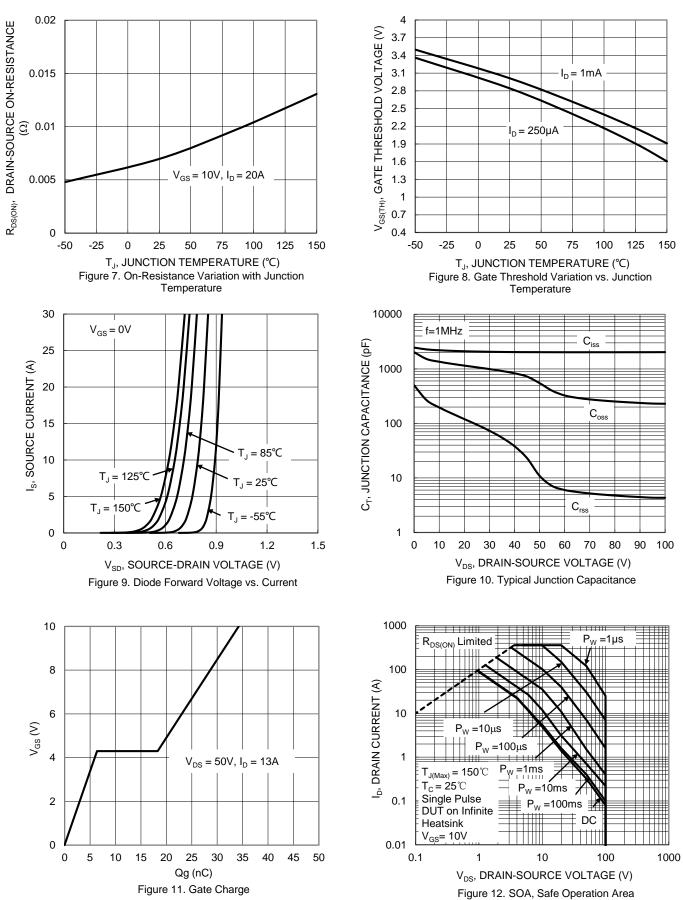
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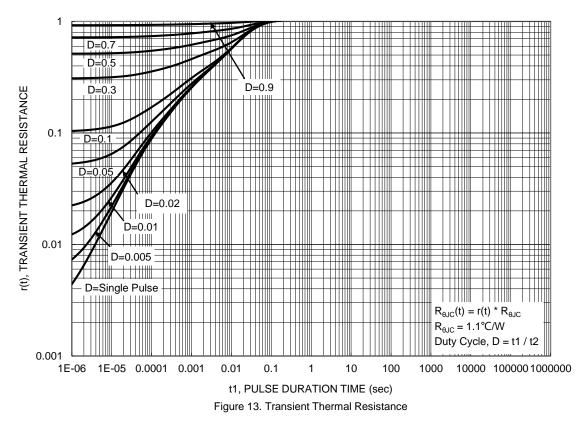
DMT10H009SK3 Document number: DS42154 Rev. 3 - 2



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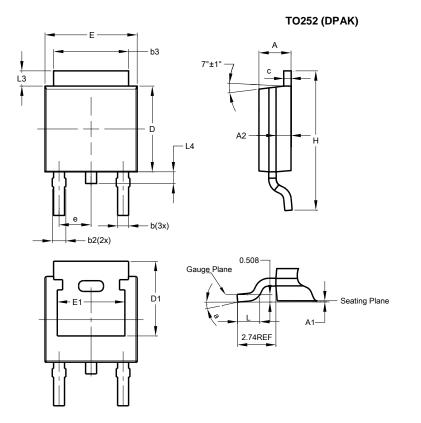






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

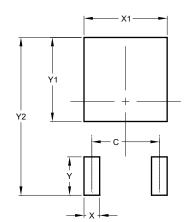


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
q	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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